

IN THE CLAIMS:

Please append claims 140 - 192.

Please amend claims 26 - 28, 30, 35 - 37, 39 - 50, 55 - 56, 59, 63, 72 - 76, 79, 86, 98 - 99, 101, 104 - 105, 111 - 112, 118, 123, 130, and 135.

1                   1 - 25. (canceled)

1                   26.     (Currently amended): A structure comprising an assemblage of  
2     separate ~~functional blocks~~electronic devices, each ~~functional block~~electronic device  
3     having a first surface and a second surface substantially parallel to said first surface, said  
4     ~~functional block~~electronic device further having side surfaces connecting said first  
5     surface to said second surface, said first surface having a smaller area than said second  
6     surface.

1                   27.     (Currently amended): The structure of claim 26 wherein said  
2     ~~functional block~~electronic device has a ~~maximum linear length~~length dimension of about 50  
3     microns or less.

1                   28.     (Currently amended): The structure of claim 26 wherein said  
2     ~~functional block~~electronic device has a trapezoidal cross-section.

1                   29.     (Previously added): The structure of claim 26 wherein said side  
2     surfaces are etched surfaces.

1                   30.     (Currently amended): The structure of claim 26 wherein said  
2     ~~functional block~~electronic device is a multilayered structure.

1                   31.     (Previously added): The structure of claim 30 wherein said  
2     multilayered structure includes a metal layer.

1                   32.     (Previously added): The structure of claim 30 wherein said  
2 multilayered structure includes an insulator layer.

1                   33.     (Previously added): The structure of claim 30 wherein said  
2 multilayered structure includes a layer of silicon dioxide.

1                   34.     (Previously added): The structure of claim 30 wherein said  
2 multilayered structure includes a layer of silicon nitride.

1                   35.     (Currently amended): The structure of claim 26 wherein said  
2 ~~functional block~~electronic device comprises material is selected from the group  
3 consisting of silicon, gallium arsenide, aluminum gallium arsenide, diamond, and  
4 germanium.

1                   36.     (Currently amended): The structure of claim 26 wherein said  
2 ~~functional block~~electronic device comprises a group III-V compound.

1                   37.     (Currently amended): The structure of claim 26 wherein said  
2 ~~functional block~~electronic device comprises a group II-VI compound.

1                   38.     (Previously added): The structure of claim 26 wherein the  
2 perimeter of said first surface has a rectangular shape, an octagonal shape, or a circular  
3 shape.

1                   39.     (Currently amended): ~~A functional block~~An electronic device  
2 comprising semiconductor material and having a tapered profile of a shape generally that  
3 of a truncated pyramid, said ~~functional block~~electronic device having a ~~maximum linear~~  
4 length dimension of ~~about 50 microns or less~~less than or equal to 1 mm in measure, said  
5 ~~functional block~~electronic device being separated from a substrate.

1                   40.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 further having a first surface and a second surface substantially parallel to said  
3    first surface.

1                   41.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 40 wherein the perimeter of said first surface has a rectangular shape, an octagonal  
3    shape, or a circular shape.

1                   42.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 wherein said semiconductor material is a multilayered structure.

1                   43.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 wherein said semiconductor material is a group III-V compound.

1                   44.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 43 wherein said semiconductor material is gallium arsenide.

1                   45.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 wherein said semiconductor material is a light-emitting diode.

1                   46.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 45 wherein said semiconductor material is a gallium arsenide light-emitting diode.

1                   47.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 wherein said semiconductor material is a laser diode.

1                   48.    (Currently amended): The ~~functional block~~electronic device of  
2    claim 39 ~~having wherein a cross-section thereof shows one of a cylindrical shape, a~~  
3    rectangular shape, a square shape, a hexagonal shape, ~~a pyramid shape, a T-shape, and a~~  
4    kidney shape.

1                   49.     (Currently amended): A shaped block of material adapted for being  
2     received in a recess of a substrate, said shaped block of material ~~comprising a solid~~  
3     having sloped sides and a top surface connected to a bottom surface by said sloped sides,  
4     said top surface being substantially parallel to said bottom surface, said top surface being  
5     non-congruent with said bottom surface.

1                   50.     (Currently amended): The shaped block of claim 49 wherein said  
2     block of material has a ~~maximum linear dimension of about 50 microns or less~~length  
3     measurement less than or equal to 50 microns.

1                   51.     (Previously added): The shaped block of claim 49 wherein said  
2     sloped sides are etched sides.

1                   52.     (Previously added): The shaped block of claim 49 wherein said  
2     sloped sides have a slope greater than about twenty degrees relative to a line normal to  
3     said top surface.

1                   53.     (Previously added): The shaped block of claim 49 wherein said  
2     material comprises a multilayered structure.

1                   54.     (Previously added): The shaped block of claim 49 wherein said  
2     material is selected from the group consisting of silicon, gallium arsenide, aluminum  
3     gallium arsenide, diamond, and germanium.

1                   55.     (Currently amended): The shaped block of claim 49 wherein said  
2     material ~~is~~comprises a group III - V compound.

1                   56.     (Currently amended): The shaped block of claim 49 wherein said  
2     material ~~is~~comprises a group II - VI compound.

1                   57.     (Previously added): The shaped block of claim 49 being an optical  
2     detector.

1                   58.     (Previously added): The shaped block of claim 49 wherein the  
2     perimeter of said first surface has a rectangular shape, an octagonal shape, or a circular  
3     shape.

1                   59.     (Currently amended): A shaped functional block comprising a  
2     semiconductor material and having a shape adapted for self-alignment within a shaped  
3     ~~opening~~ recess formed through a substrate surface, said block having a first surface and a  
4     second surface and having etched sides which are sloped such that said block fits into  
5     said shaped opening only in an orientation where said first surface is exposed through  
6     said substrate surface.

1                   60.     (Previously added): The functional block of claim 59 wherein said  
2     first surface includes a conductive contact disposed thereon.

1                   61.     (Previously added): The functional block of claim 59 wherein said  
2     first surface has an area smaller than said second surface.

1                   62.     (Previously added): The functional block of claim 61 wherein said  
2     first surface has a circular perimeter, a rectilinear perimeter, or an octagonal perimeter.

1                   63.     (Currently amended): The functional block of claim 59 having a  
2     maximum ~~linear-length~~ dimension of about ~~50 microns~~ 1 mm or less.

1                   64.     (Previously added): The functional block of claim 59 further  
2     comprising a multilayered structure.

1                   65.     (Previously added): The functional block of claim 64 wherein said  
2     multilayered structure includes a metal layer.

1                   66.     (Previously added): The functional block of claim 64 wherein said  
2     multilayered structure includes an insulator layer.

1                   67.     (Previously added): The functional block of claim 64 wherein said  
2 multilayered structure includes a layer of silicon dioxide.

1                   68.     (Previously added): The functional block of claim 64 wherein said  
2 multilayered structure includes a layer of silicon nitride.

1                   69.     (Previously added): The functional block of claim 59 being a light-  
2 emitting diode.

1                   70.     (Previously added): The functional block of claim 59 being a laser  
2 diode.

1                   71.     (Previously added): The functional block of claim 59 being an  
2 optical detector.

1                   72.     (Currently amended): A semiconductor microstructure comprising  
2 a ~~wedge-shaped~~shaped block having a first surface substantially parallel to a second  
3 surface, said first surface having an associated first area, said second surface having an  
4 associated second area, said first area being larger than said second area, an edge adjacent  
5 said first surface being sloped, said block having a maximum ~~linear~~length dimension of  
6 about ~~50 microns~~1 mm or less in measure.

1                   73.     (Currently amended): The semiconductor microstructure of claim  
2 72 wherein said ~~wedge-shaped~~shaped block comprises material selected from the group  
3 consisting of silicon, gallium arsenide, aluminum gallium arsenide, diamond, and  
4 germanium.

1                   74.     (Currently amended): The semiconductor microstructure of claim  
2 72 wherein said ~~wedge-shaped~~shaped block comprises a group III-V compound.

1                   75.     (Currently amended): The semiconductor microstructure of claim  
2 72 wherein said ~~wedge-shaped~~shaped block comprises a group II-VI compound.

1                   76.     (Currently amended): The semiconductor microstructure of claim  
2     72 wherein said ~~wedge-shaped~~shaped block is a multilayered structure.

1                   77.     (Previously added): The semiconductor microstructure of claim 76  
2     wherein said multilayered structure constitutes a light-emitting diode.

1                   78.     (Previously added): The semiconductor microstructure of claim 77  
2     wherein said multilayered structure includes gallium arsenide.

1                   79.     (Currently amended): A portion of an integrated circuit device  
2     comprising a shaped functional block ~~separated from a substrate~~, said functional block  
3     comprising a semiconductor material and having a ~~maximum linear~~length dimension of  
4     ~~about 50 microns or less~~less than or equal to 1 mm in measure, ~~said functional block~~  
5     ~~having a wedge-shaped profile~~, said functional block having etched sides.

1                   80.     (Previously added): The portion of an integrated circuit device of  
2     claim 79 wherein said semiconductor material is a multilayered structure.

1                   81.     (Previously added): The portion of an integrated circuit device of  
2     claim 79 wherein said semiconductor material is selected from the group consisting of  
3     silicon, gallium arsenide, aluminum gallium arsenide, diamond, and germanium.

1                   82.     (Previously added): The portion of an integrated circuit device of  
2     claim 79 wherein said semiconductor material is a group III-V compound.

1                   83.     (Previously added): The portion of an integrated circuit device of  
2     claim 79 wherein said semiconductor material is a group II-VI compound.

1                   84.     (Previously added): The portion of an integrated circuit device of  
2     claim 79 wherein said semiconductor material constitutes a light-emitting diode.

1                   85.     (Previously added): The portion of an integrated circuit device of  
2     claim 84 wherein said light-emitting diode is a gallium arsenide light-emitting diode.

1                   86.     (Currently amended): An electronic chip comprising a shaped  
2     block of material separated from a substrate and having a first surface and a second  
3     surface substantially parallel to said first surface, said block further having etched side  
4     surfaces extending from said first surface to said second surface, said first surface having  
5     an areal measurement different than an areal measurement of said second surface, said  
6     first surface having a conductive contact disposed thereon.

1                   87.     (Previously added): The electronic chip of claim 86 wherein said  
2     block of material has a width of about 50 microns or less and a length of about 50  
3     microns or less.

1                   88.     (Previously added): The electronic chip of claim 86 wherein said  
2     etched side surfaces have a slope relative to a line normal to said first surface of greater  
3     than about twenty degrees.

1                   89.     (Previously added): The electronic chip of claim 86 wherein said  
2     material comprises a multilayered structure including one or more layers of  
3     semiconductor material.

1                   90.     (Previously added): The electronic chip of claim 89 wherein said  
2     multilayered structure includes a silicon layer and a gallium arsenide layer.

1                   91.     (Previously added): The electronic chip of claim 89 wherein said  
2     multilayered structure includes a p-type gallium arsenide layer, an n-type gallium  
3     arsenide layer, and a eutectic layer.

1                   92.     (Previously added): The electronic chip of claim 91 wherein said  
2     multilayered structure further includes a silicon substrate layer.



1                   93.     (Previously added): The electronic chip of claim 86 wherein said  
2     material is semiconductor material.

1                   94.     (Previously added): The electronic chip of claim 86 wherein said  
2     electronic chip is a light-emitting diode.

1                   95.     (Previously added): The electronic chip of claim 86 wherein said  
2     electronic chip is a gallium arsenide resonant tunneling diode.

1                   96.     (Previously added): The electronic chip of claim 86 wherein said  
2     electronic chip is a gallium arsenide diode.

1                   97.     (Previously added): The electronic chip of claim 86 wherein said  
2     electronic chip is a gallium arsenide microwave device.

1                   98.     (Currently amended): The electronic chip of claim 86 ~~having~~  
2     wherein a cross-section thereof shows one of a cylindrical shape, a rectangular shape, a  
3     square shape, a hexagonal shape, ~~a pyramid shape~~, a T-shape, and a kidney shape.

1                   99.     (Currently amended): An electronic chip comprising a shaped  
2     functional block including a semiconductor material, said functional block having a  
3     ~~wedge shape~~tapered sides with a top surface and a bottom surface smaller than said top  
4     surface, said functional block further having a ~~maximum linear dimension of about 50~~  
5     ~~microns or less, the~~length measurement less than or equal to 1 mm, a perimeter of said  
6     top surface having a rectilinear shape, a circular shape, or an octagonal shape.

1                   100.    (Previously added): The electronic chip of claim 99 wherein said  
2     top surface is substantially parallel to said bottom surface.

1                   101.    (Currently amended): The electronic chip of claim 99 further  
2     including a conductive contact disposed atop either or both said top surface and said  
3     bottom surface.

1                   102.   (Previously added): The electronic chip of claim 99 wherein said  
2 semiconductor material is a multilayered structure.

1                   103.   (Previously added): The electronic chip of claim 102 wherein said  
2 multilayered structure constitutes a light-emitting diode.

1                   104.   (Currently amended): An electronic component separated from a  
2 first substrate comprising:  
3                   a first surface;  
4                   a conductive contact disposed atop said first surface;  
5                   a second surface in substantially parallel relation to said first surface; and  
6                   etched surfaces connecting said first surface to said second surface,  
7                   said etched surfaces being ~~in non-parallel relation to one another~~tapered to  
8 define at least a beveled edge adjacent said first surface,  
9                   wherein said electronic component is adapted for self-alignment within a  
10 shaped opening through a surface of a second substrate.

1                   105.   (Currently amended): The electronic component of claim 104  
2 wherein said amount of semiconductor material has a maximum ~~linear dimension~~length  
3 measurement of about 50 microns or less.

1                   106.   (Previously added): The electronic component of claim 104  
2 wherein said etched surfaces are formed by a wet etch process.

1                   107.   (Previously added): The electronic component of claim 104  
2 wherein said etched surfaces are formed by a mask edge.

1                   108.   (Previously added): The electronic component of claim 104  
2 wherein said etched surfaces are formed by a reactive ion etch process.

1                   109.   (Previously added): The electronic component of claim 104  
2   wherein said etched surfaces are formed by an ion milling process.

1                   110.   (Previously added): The electronic component of claim 104 being  
2   a light-emitting diode.

1                   111.   (Currently amended): A light-emitting diode (LED) comprising a  
2   shaped semiconductor block having tapered sides, said semiconductor block comprising a  
3   first surface and a second surface in substantially parallel relation to said first surface,  
4   said tapered sides defining at least a beveled edge adjacent at least one of said first and  
5   second surfaces.

1                   112.   (Currently amended): The LED of claim 111 wherein said  
2   semiconductor block has a maximum linear length dimension of about 50 microns or  
3   less less than or equal to 50 microns in measure.

1                   113.   (Previously added): The LED of claim 111 wherein said tapered  
2   sides are etched sides.

1                   114.   (Previously added): The LED of claim 111 incorporated in an  
2   active display.

1                   115.   (Previously added): The LED of claim 111 wherein said  
2   semiconductor block is a multilayered structure.

1                   116.   (Previously added): The LED of claim 115 wherein said  
2   multilayered structure includes gallium arsenide.

1                   117.   (Previously added): The LED of claim 115 wherein said  
2   multilayered structure includes a group III-V compound.

1                   118. (Currently amended): A light-emitting diode (LED) comprising an  
2 amount of semiconductor material, said semiconductor material having a first surface and  
3 a second surface smaller than said first surface, said semiconductor material having non-  
4 parallel side surfaces connecting said first surface to said second surface, said LED  
5 having a ~~maximum linear~~length dimension ~~of about 50 microns or less~~ than or equal to 1  
6 mm.

1                   119. (Previously added): The LED of claim 118 wherein said first  
2 surface is in substantially parallel relation to said second surface.

1                   120. (Previously added): The LED of claim 118 wherein said  
2 semiconductor material includes a group III-V compound.

1                   121. (Previously added): The LED of claim 120 wherein said  
2 semiconductor material includes gallium arsenide.

1                   122. (Previously added): The LED of claim 118 wherein the perimeter  
2 of said first surface has a rectangular shape, an octagonal shape, or a circular shape.

1                   123. (Currently amended): A light-emitting diode (LED) comprising a  
2 block of semiconductor material including gallium arsenide, said block having a top  
3 surface and a bottom surface connected to said top surface by sloped surfaces, said top  
4 and bottom surfaces having different areal measurements, said block having a ~~maximum~~  
5 ~~linear dimension~~length measurement of about ~~50 microns~~ 1 mm or less.

1                   124. (Previously added): The LED of claim 123 wherein said sloped  
2 surfaces are etched surfaces.

1                   125. (Previously added): The LED of claim 124 wherein said etched  
2 surfaces are formed by a wet etch process.

1                   126.   (Previously added): The LED of claim 124 wherein said etched  
2 surfaces are formed by a mask edge.

1                   127.   (Previously added): The LED of claim 124 wherein said etched  
2 surfaces are formed by a reactive ion etch process.

1                   128.   (Previously added): The LED of claim 124 wherein said etched  
2 surfaces are formed by an ion milling process.

1                   129.   (Previously added): The LED of claim 123 wherein the perimeter  
2 of said top surface has a rectangular shape, an octagonal shape, or a circular shape.

1                   130.   (Currently amended): A laser diode comprising a ~~wedge-~~  
2 ~~shaped~~shaped block of semiconductor material having a ~~maximum linear length~~  
3 dimension of about ~~50 microns~~ 1 mm or less in measure, said block of semiconductor  
4 having a tapered edge.

1                   131.   (Previously added): The laser diode of claim 130 wherein said  
2 semiconductor material comprises a group III-V compound.

1                   132.   (Previously added): The laser diode of claim 131 wherein said  
2 semiconductor material comprises gallium arsenide.

1                   133.   (Previously added): The laser diode of claim 130 wherein said  
2 block comprises first and second surfaces in parallel relation and etched side surfaces  
3 connecting said first and second surfaces, said first surface having an area different than  
4 an area of said second surface.

1                   134.   (Previously added): The laser diode of claim 130 incorporated in  
2 an optical data channel.

1                   135. (Currently amended): An optical detector comprising a ~~wedge-~~  
2 ~~shaped~~shaped block of semiconductor material having a ~~maximum linear~~  
3 ~~dimension~~length measurement of about ~~50 microns~~1 mm or less, said block of  
4 semiconductor material having a beveled edge adjacent a major surface thereof.

1                   136. (Previously added): The optical detector of claim 135 wherein said  
2 semiconductor material comprises a group III-V compound.

1                   137. (Previously added): The optical detector of claim 136 wherein said  
2 semiconductor material comprises gallium arsenide.

1                   138. (Previously added): The optical detector of claim 135 wherein said  
2 block comprises first and second surfaces in parallel relation and etched side surfaces  
3 connecting said first and second surfaces, said first surface having an area different than  
4 an area of said second surface.

1                   139. (Previously added): The optical detector of claim 135 incorporated  
2 in an optical data channel.

1                   140. (New): The structure of claim 26 wherein said electronic device  
2 has a length dimension of about 1 mm or less.

1                   141. (New): The structure of claim 26 wherein said electronic device  
2 has a length dimension of about 500 microns or less.

1                   142. (New): The structure of claim 26 wherein said electronic device  
2 has an edge portion that is beveled.

1                   143. (New): The structure of claim 26 wherein said electronic device is  
2 shaped like a truncated pyramid.

1                   144.   (New): The electronic device of claim 39 wherein said length  
2   dimension less than or equal to 500 microns.

1                   145.   (New): The electronic device of claim 39 wherein said length  
2   dimension is less than or equal to 50 microns.

1                   146.   (New): The electronic device of claim 39 wherein said profile has  
2   a trapezoidal shape.

1                   147.   (New): The electronic device of claim 39 wherein said profile  
2   shows at least a partially beveled edge.

1                   148.   (New): The electronic device of claim 39 having one of a pyramid  
2   shape and a truncated pyramid shape.

1                   149.   (New): The shaped block of claim 49 wherein said block of  
2   material has a length measurement less than or equal to 500 microns.

1                   150.   (New): The shaped block of claim 49 wherein said block of  
2   material has a length measurement less than or equal to 1 mm.

1                   151.   (New): The shaped block of claim 49 wherein said sloped sides  
2   have a trapezoidal profile.

1                   152.   (New): The shaped block of claim 49 wherein said sloped sides  
2   define a portion of a beveled edge.

1                   153.   (New): The shaped block of claim 49 wherein said shaped block  
2   has a shape of a truncated pyramid.

1                   154.   (New): The functional block of claim 59 having a maximum length  
2   dimension of about 500 micron or less.

1                   155.   (New): The functional block of claim 59 having a maximum length  
2   dimension of about 50 micron or less.

1                   156.   (New): The functional block of claim 59 wherein said etched sides  
2   are characterized by having a trapezoidal profile.

1                   157.   (New): The functional block of claim 59 wherein said etched sides  
2   form a beveled edge adjacent said first surface.

1                   158.   (New): The functional block of claim 59 having a shape of a  
2   truncated pyramid.

1                   159.   (New): The semiconductor microstructure of claim 72 wherein said  
2   length dimension further is about 500 microns or less in measure.

1                   160.   (New): The semiconductor microstructure of claim 159 wherein  
2   said length dimension further is about 50 microns or less in measure.

1                   161.   (New): The semiconductor microstructure of claim 72 wherein said  
2   edge has a trapezoidal profile.

1                   162.   (New): The semiconductor microstructure of claim 72 wherein said  
2   edge is beveled.

1                   163.   (New): The semiconductor microstructure of claim 72 wherein said  
2   shaped block has a truncated pyramid appearance.

1                   164.   (New): The portion of an integrated circuit device of claim 79  
2   wherein said length dimension further is less than or equal to 500 microns in measure.

1                   165.   (New): The portion of an integrated circuit device of claim 164  
2   wherein said length dimension further is less than or equal to 50 microns in measure.



1                   166. (New): The portion of an integrated circuit device of claim 79  
2 wherein said etched sides have a form a trapezoidal profile.

1                   167. (New): The portion of an integrated circuit device of claim 79  
2 wherein said functional block further comprises a first major surface and a second major  
3 surface connected to said first major surface by said etched sides, a portion of said etched  
4 sides adjacent to said first major surface forming a beveled edge.

1                   168. (New): The portion of an integrated circuit device of claim 79  
2 wherein said functional block has a shape of a truncated pyramid.

1                   169. (New): The electronic chip of claim 86 wherein said block of  
2 material has a width of about 1 mm or less and a length of about 1 mm or less.

1                   170. (New): The electronic chip of claim 86 wherein said block of  
2 material has a width of about 500 microns or less and a length of about 500 microns or  
3 less.

1                   171. (New): The electronic chip of claim 86 wherein said shaped block  
2 has an outwardly sloped profile.

1                   172. (New): The electronic chip of claim 86 wherein said shaped block  
2 has an inwardly sloped profile.

1                   173. (New): The electronic chip of claim 86 wherein a profile of said  
2 shaped block resembles a trapezoid.

1                   174. (New): The electronic chip of claim 86 wherein said etched side  
2 surfaces define a beveled edge adjacent said first surface.

1                   175. (New): The electronic chip of claim 86 wherein said shaped block  
2 is one of a pyramid shape and a truncated pyramid shape.

1                   176. (New): The electronic chip of claim 99 wherein said length  
2 measurement further is less than or equal to 500 microns.

1                   177. (New): The electronic chip of claim 176 wherein said length  
2 measurement further is less than or equal to 50 microns.

1                   178. (New): The electronic chip of claim 99 wherein said tapered sides  
2 define at least a beveled edge adjacent said top surface.

1                   179. (New): The electronic component of claim 104 wherein said  
2 amount of semiconductor material has a maximum length measurement of about 1 mm or  
3 less.

1                   180. (New): The electronic component of claim 104 wherein said  
2 amount of semiconductor material has a maximum length measurement of about 500  
3 microns or less.

1                   181. (New): The LED of claim 111 wherein said semiconductor block  
2 has a length dimension less than or equal to 1 mm in measure.

1                   182. (New): The LED of claim 111 wherein said semiconductor block  
2 has a length dimension less than or equal to 500 microns in measure.

1                   183. (New): The LED of claim 118 wherein said length dimension  
2 further is less than or equal to 500 microns.

1                   184. (New): The LED of claim 183 wherein said length dimension  
2 further is less than or equal to 50 microns.

1                   185. (New): The LED of claim 118 further comprising a beveled edge  
2 formed adjacent one of said first and second surfaces.

1                   186.   (New): The LED of claim 123 wherein said length measurement  
2 further is about 500 microns or less.

1                   187.   (New): The LED of claim 186 wherein said length measurement  
2 further is about 50 microns or less.

1                   188.   (New): The LED of claim 124 wherein said sloped surfaces define  
2 a beveled edge adjacent one of said top and bottom surfaces.

1                   189.   (New): A shaped block of semiconductor material having tapered  
2 sides, said block of material comprising a first surface and a second surface in  
3 substantially parallel relation to said first surface, said tapered sides defining a beveled  
4 edge adjacent at least one of said first and second surfaces.

1                   190.   (New): The shaped block of claim 189 having a maximum length  
2 dimension less than or equal to 1 mm in measure.

1                   191.   (New): The shaped block of claim 189 having a maximum length  
2 dimension less than or equal to 500 microns in measure.

1                   192.   (New): The shaped block of claim 189 having a maximum length  
2 dimension less than or equal to 50 microns in measure.